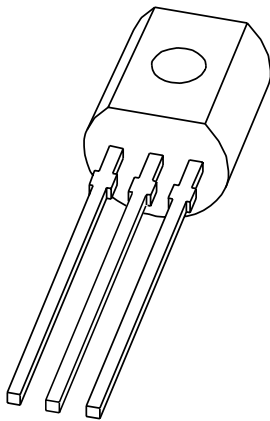


# DATA SHEET



## **BC549; BC550** NPN general purpose transistors

Product specification  
Supersedes data of 1997 Jun 20

1999 Apr 22

NPN general purpose transistors

BC549; BC550

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

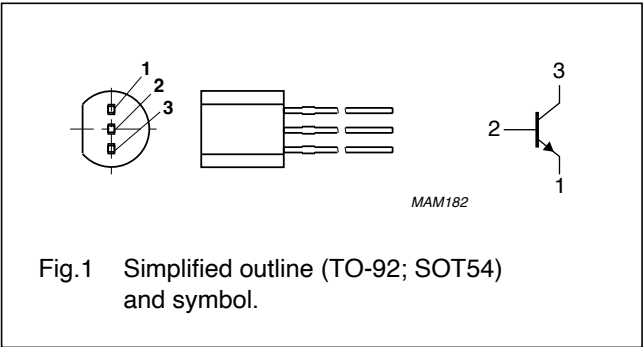
- Low noise stages in audio frequency equipment.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.  
PNP complements: BC559 and BC560.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC549		–	30	V
	BC550		–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC549		–	30	V
	BC550		–	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
I <sub>BM</sub>	peak base current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	500	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN general purpose transistors

## BC549; BC550

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	–	5	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain BC549C; BC550C	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; \text{ see Fig.2}$	–	270	–	
		$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{ see Fig.2}$	420	520	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; \text{ note 1}$	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{ note 1}$	–	900	–	mV
$V_{BE}$	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{ note 2}$	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; \text{ note 2}$	–	–	770	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	1.5	–	pF
$C_e$	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	11	–	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
		$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

## Notes

1.  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.
2.  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.